N-channel 60 V, 11.5 mOhm, logic level Trench MOSFET in MLPAK33

8 July 2021

Product data sheet

1. General description

General purpose, 42 A rated, logic level N-channel enhancement mode Power MOSFET in MLPAK33 package.

2. Features and benefits

- Logic level compatibility
- Trench MOSFET technology
- Thermally efficient package in a small form factor (3.3 mm x 3.3 mm footprint)

3. Applications

- Secondary side synchronous rectification
- DC-to-DC converters
- Motor drive
- LED lighting
- Load switching
- Auxiliary control
- Fan control

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C		-	-	60	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C; <u>Fig. 2</u>		-	-	42	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>		-	-	34.7	W
Tj	junction temperature			-55	-	150	°C
Static chara	acteristics			•	'	'	'
R _{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 9$		-	9.8	11.5	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C}; Fig. 9$		-	14	17.6	mΩ
Dynamic ch	naracteristics				'		
Q_{GD}	gate-drain charge	I _D = 10 A; V _{DS} = 30 V; V _{GS} = 4.5 V;		-	4.3	-	nC
Q _{G(tot)}	total gate charge	T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>		-	9.64	-	nC
Avalanche i	ruggedness			•	'	'	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I _D = 3.5 A; T _{j(init)} = 25 °C; unclamped	[1]	-	-	90	mJ



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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain d	Source-drain diode						
Q _r		$I_S = 10 \text{ A}; \text{ dI}_S/\text{dt} = -100 \text{ A/}\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 30 \text{ V}; \text{ T}_j = 25 ^{\circ}\text{C}; \frac{\text{Fig. } 15}{\text{C}}$	[2]	-	13	-	nC

- [1] Protected by 100% test
- [2] includes capacitive recovery

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	
2	S	source		
3	S	source		D ⊥
4	G	gate]	
5	D	drain		G—UFIA)
6	D	drain	Laaad	mbb076 S
7	D	drain	8 7 6 5 MI DAK22 (COT9002 4)	
8	D	drain	MLPAK33 (SOT8002-1)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PXN012-60QL		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1		

7. Marking

Table 4. Marking codes

Type number	Marking code
PXN012-60QL	7AB

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>		-	34.7	W
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C; <u>Fig. 2</u>		-	42	Α
		V _{GS} = 10 V; T _{sp} = 100 °C; <u>Fig. 2</u>		-	26	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{sp} = 25 °C; <u>Fig. 3</u>		-	168	Α
T _{stg}	storage temperature			-55	150	°C
T _j	junction temperature			-55	150	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	n diode					'
Is	source current	T _{sp} = 25 °C		-	29	Α
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{sp} = 25 °C		-	168	Α
Avalanche r	uggedness		'	<u> </u>	'	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I _D = 3.5 A; T _{j(init)} = 25 °C; unclamped	[1]	-	90	mJ
I _{AS}	non-repetitive avalanche current	$T_{j(init)} = 25 ^{\circ}C$	[1]	-	3.5	А

[1] Protected by 100% test

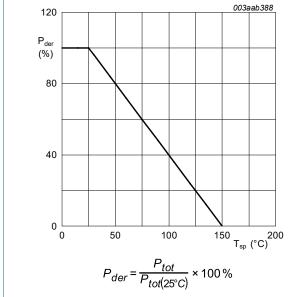


Fig. 1. Normalized total power dissipation as a function of solder point temperature

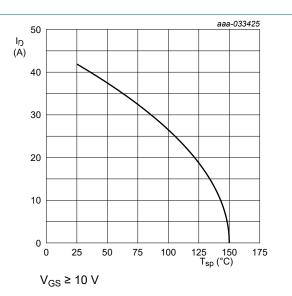
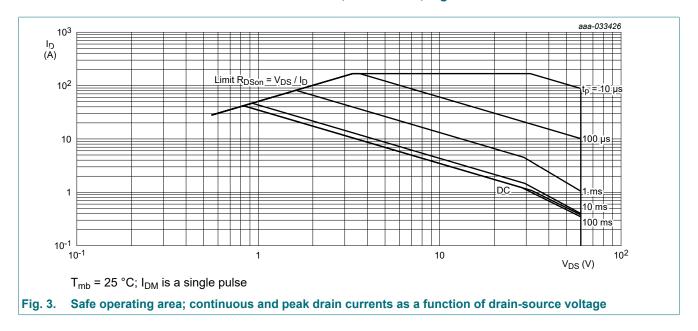


Fig. 2. Continuous drain current as a function of mounting base temperature

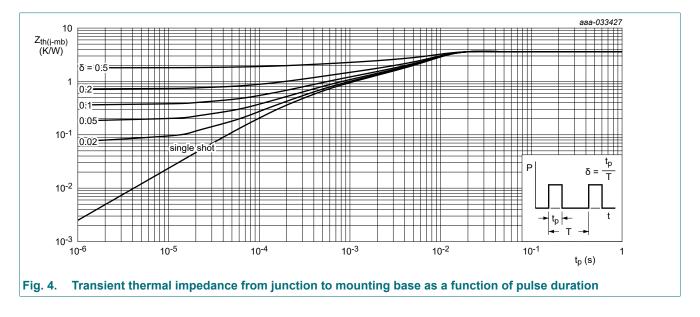
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from	Fig. 4	-	3	3.6	K/W
	junction to solder point					



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	60	70	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	-	64	-	V
V _{GS(th)}	gate-source threshold	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 8</u>	1.5	1.9	2.5	V
	voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 150 °C	0.9	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.9	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-4.7	-	mV/K
I _{DSS} c	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	1	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 9</u>	-	9.8	11.5	mΩ
	resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 150 ^{\circ}\text{C};$ Fig. 10	-	-	20	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C}; Fig. 9$	-	14	17.6	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 150 ^{\circ}\text{C};$ Fig. 10	-	-	30	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	-	1.66	-	Ω
Dynamic cha	racteristics			'	1	
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 30 V; V _{GS} = 4.5 V; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	-	9.64	-	nC
		I _D = 10 A; V _{DS} = 30 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	-	18.77	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 4.5 V; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	-	9.54	-	nC
Q _{GS}	gate-source charge	I _D = 10 A; V _{DS} = 30 V; V _{GS} = 4.5 V;	-	3	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	-	1.6	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	1.4	-	nC
Q_{GD}	gate-drain charge		-	4.3	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 10 A; V _{DS} = 30 V; T _j = 25 °C; Fig. 11; Fig. 12	-	3.1	-	V
C _{iss}	input capacitance	V _{DS} = 30 V; V _{GS} = 0 V; f = 1 MHz;	-	957	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 13</u>	-	386	-	pF
C _{rss}	reverse transfer capacitance		-	31	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 3 \Omega; V_{GS} = 4.5 \text{ V};$	-	8.8	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$	-	18.5	-	ns
$t_{d(off)}$	turn-off delay time	1	-	12.2	-	ns
t _f	fall time		-	10.9	-	ns

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	18	-	nC
Source-drain diode							
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 14$		-	0.82	1.2	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	22.1	-	ns
Q _r	recovered charge	V _{DS} = 30 V; T _j = 25 °C; <u>Fig. 15</u>		-	13	-	nC

[1] includes capacitive recovery

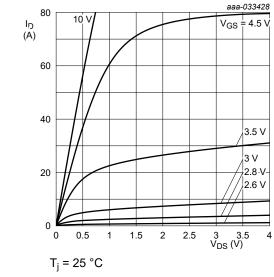


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values

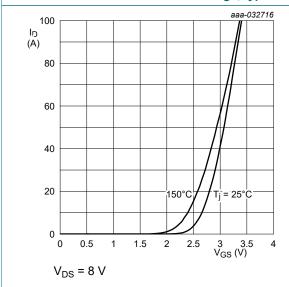


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

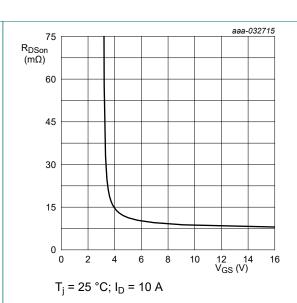


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

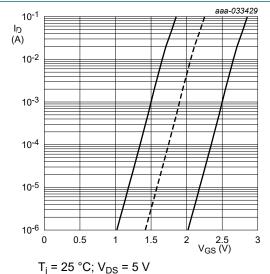


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

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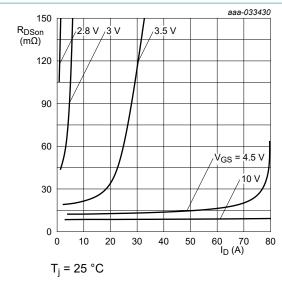


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

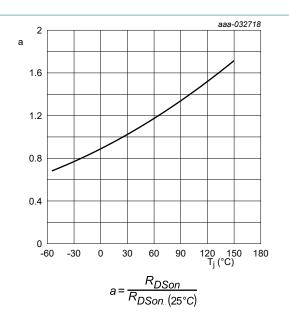


Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature

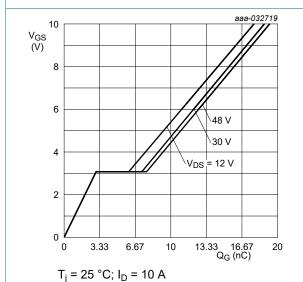


Fig. 11. Gate-source voltage as a function of gate charge; typical values

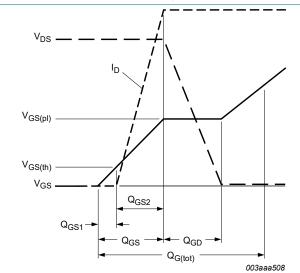
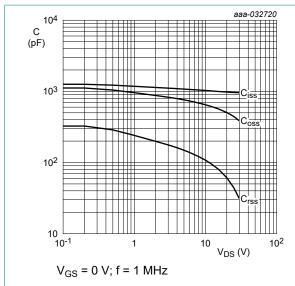


Fig. 12. Gate charge waveform definitions

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as a function of drain-source voltage; typical values

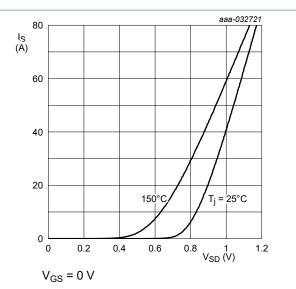


Fig. 13. Input, output and reverse transfer capacitances | Fig. 14. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

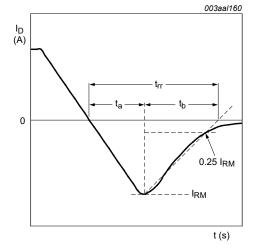
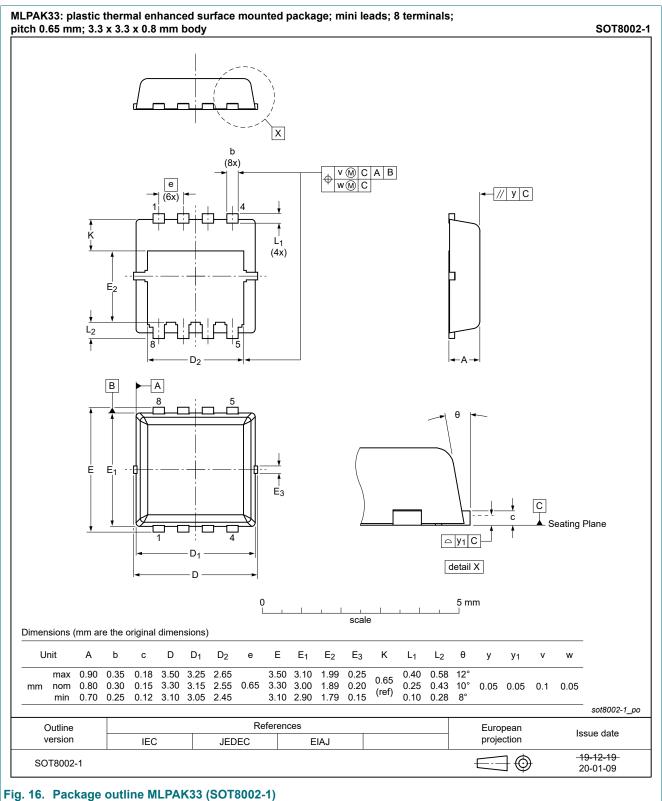


Fig. 15. Reverse recovery timing definition

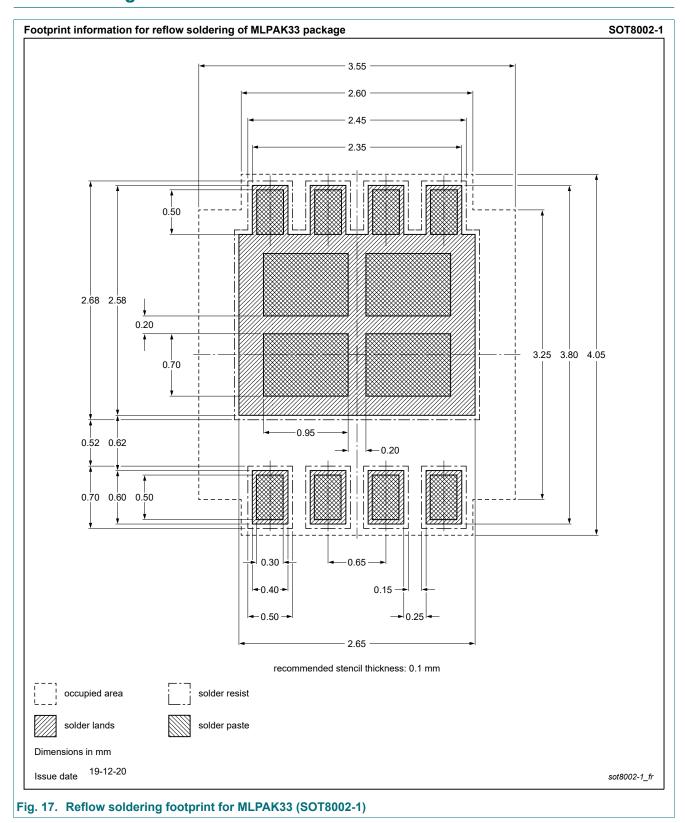
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11. Package outline



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12. Soldering



PXN012-60QL

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